

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	105mΩ
$I_{D}^{^{*1}}$	23A
P_D	125W

Outline TO-263-7L

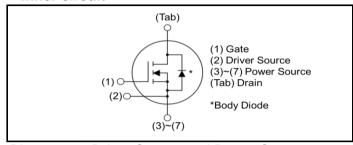
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Type	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT3105KW7

● Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V _{DSS}	1200	V
Continuous Drain current	$T_c = 25^{\circ}C$	I _D *1	23	Α
Continuous Diam current	T _c = 100°C	I _D *1	16	Α
Pulsed Drain current		I _{D,pulse} *2	57	Α
Gate - Source voltage (DC)		V_{GSS}	-4 to +22	V
Gate - Source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *3	-4 to +26	V
Recommended drive voltage		$V_{GS_op}^{^{*4}}$	0 / +18	V
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
rarameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 0V$, $I_D = 1mA$				
Drain - Source breakdown voltage	V _{(BR)DSS}	$T_j = 25^{\circ}C$	1200	-	-	V
voltago		T _j = -55°C	1200	-	-	
		$V_{GS} = 0V, V_{DS} = 1200V$				
Zero Gate voltage Drain current	I _{DSS}	T _j = 25°C	-	1	10	μΑ
Drain ourion		T _j = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, \ V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	ı	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_{D} = 3.81 \text{mA}$	2.7	1	5.6	V
		$V_{GS} = 18V, I_D = 7.6A$				
Static Drain - Source on - state resistance	R _{DS(on)} *5	$T_j = 25^{\circ}C$	-	105	137	mΩ
		T _j = 150°C	-	179	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	13	-	Ω

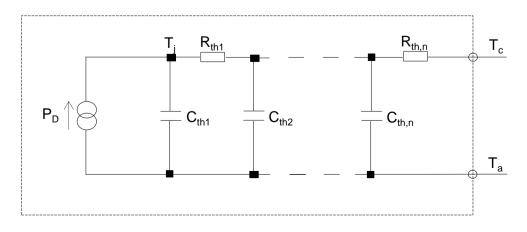
●Thermal resistance

Parameter	Symbol	Values			Unit
Falametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	0.90	1.2	°C/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.16×10 ⁻¹	
R _{th2}	3.80×10 ⁻¹	K/W
R _{th3}	3.19×10 ⁻¹	

Symbol	Value	Unit
C_{th1}	5.54×10 ⁻⁴	
C_{th2}	4.74×10 ⁻³	Ws/K
C _{th3}	8.86×10 ⁻³	



●Electrical characteristics (T_a = 25°C)

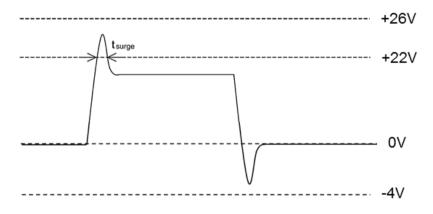
Dorometer	Cumbal	Conditions	Conditions	Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g fs *5	$V_{DS} = 10V, I_D = 7.6A$	-	3.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	574	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	59	ı	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	28	ı	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 600V$	-	159	ı	pF
Total Gate charge	Qg *5	$V_{DS} = 600V$ $I_{D} = 7.6A$	-	51	ı	
Gate - Source charge	Q _{gs} *5	$V_{GS} = 18V$	-	10	ı	nC
Gate - Drain charge	Q _{gd} *5	See Fig. 1-1.	-	25	-	
Turn - on delay time	t _{d(on)} *5	$V_{DS} = 600V$ $I_{D} = 7.6A$	-	4	ı	
Rise time	t _r *5	$V_{GS} = 0V/+18V$	-	12	-	no
Turn - off delay time	t _{d(off)} *5	$R_G = 0\Omega, L = 750\mu H$ $L_{\sigma} = 50nH, C_{\sigma} = 10pF$	-	16	1	ns
Fall time	t _f *5	See Fig. 2-1, 2-2, 2-3.	-	10	-	
Turn - on switching loss	E _{on} *5	E _{on} includes diode reverse recovery.	-	125	-	11.1
Turn - off switching loss	E _{off} *5		-	8	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Body diode continuous, forward current	I _S *1	T _c = 25°C	ı	ı	23	А
Body diode direct current, pulsed	I _{SM} *2	11 _c = 23 0	ı	ı	57	Α
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_{D} = 7.6A$	ı	3.2	ı	V
Reverse recovery time	t _{rr} *5	$I_F = 7.6A$ $V_R = 600V$	ı	13	ı	ns
Reverse recovery charge	Q _{rr} *5	di/dt = 2500A/µs	ı	175	ı	nC
Peak reverse recovery current	I _{rrm} *5	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	22	-	А

^{*1} Limited by maximum temperature allowed.

*3 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

*5 Pulsed

^{*2} $P_W \le 10\mu s$, Duty cycle $\le 1\%$

^{*4} Please be advised not to use SiC-MOSFETs with V_{GS} below 13V as doing so may cause thermal runaway.

Fig.1 Power Dissipation Derating Curve

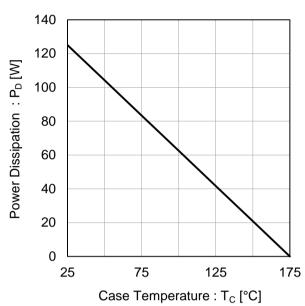


Fig.2 Maximum Safe Operating Area

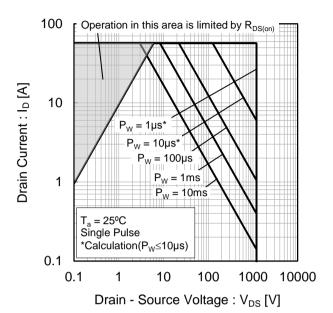


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

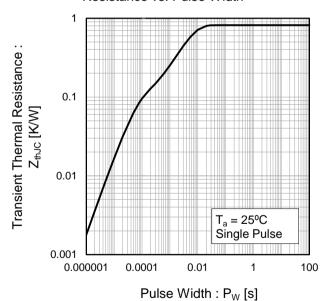


Fig.4 Typical Output Characteristics(I)

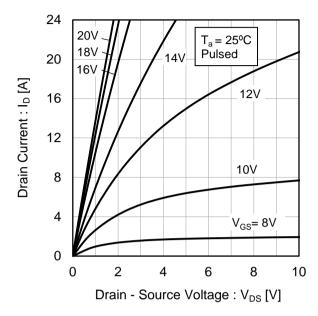


Fig.5 Typical Output Characteristics(II)

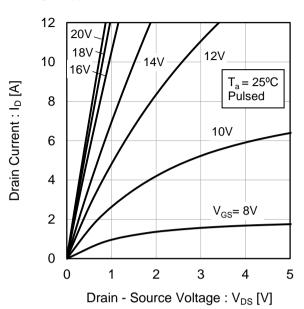


Fig.6 T_i = 25°C 3rd Quadrant Characteristics

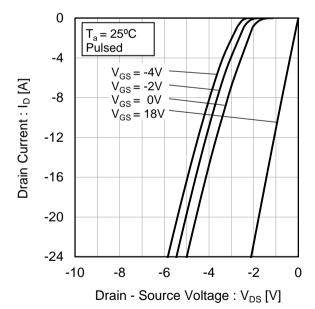


Fig.7 T_i = 150°C Typical Output Characteristics(I) 24 20V 12V 18V 20 16V Drain Current: I_D [A] 16 10V 12 8 V_{GS}= 8V 4 $T_a = 150^{\circ}C$ Pulsed 0 2 4 6 0 8 10 Drain - Source Voltage : V_{DS} [V]

Fig.8 T_i = 150°C Typical Output

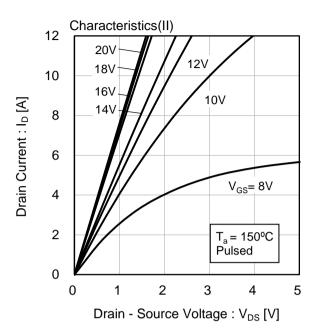


Fig.9 T_i = 150°C 3rd Quadrant Characteristics

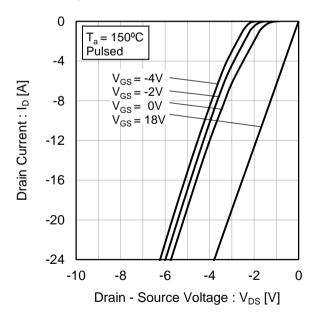


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage

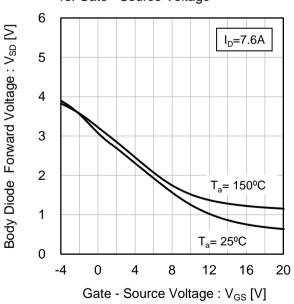


Fig.11 Typical Transfer Characteristics (I)

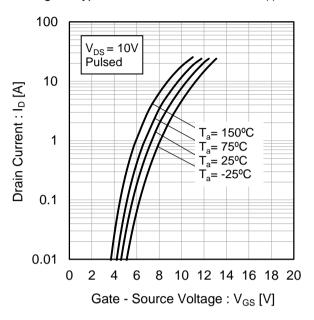


Fig.12 Typical Transfer Characteristics (II)

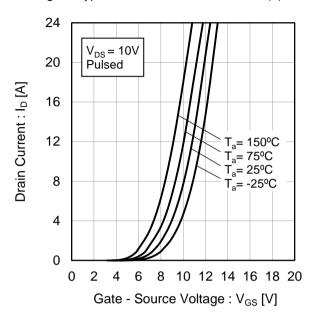


Fig.13 Gate Threshold Voltage vs. Junction Temperature

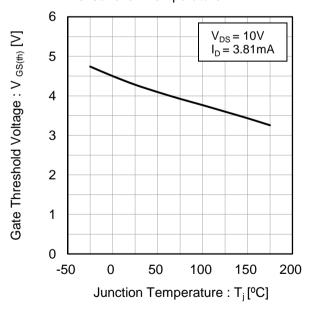
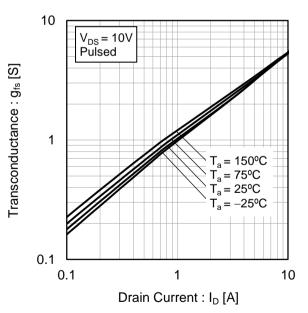
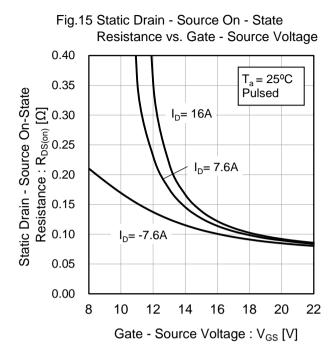


Fig.14 Transconductance vs. Drain Current





Resistance vs. Junction Temperature 0.30 $V_{GS} = 18V$ Pulsed Static Drain - Source On-State 0.24 Resistance : $R_{DS(on)}\left[\Omega\right]$ $I_D = 16A$ 0.18 I_D= 7.6A 0.12 $I_{D} = -7.6A$ 0.06 0.00 -50 0 50 100 150 200 Junction Temperature : T_i [°C]

Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current 1 Static Drain - Source On-State Resistance: R_{DS(on)} [Ω] 0.1 $T_a = 150^{\circ}C$ Ta = 125ºC = 75°C = 25°C $V_{GS} = 18V$ $T_a = -25^{\circ}C$ Pulsed 0.01 10 100 Drain Current : I_D [A]

Voltage vs. Junction Temperature 1.04 1.03 Normalized Drain - Source Breakdown Voltage 1.02 1.01 1.00 0.99 0.98 -50 0 50 100 200 150 Junction Temperature : T_i [°C]

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Fig.18 Normalized Drain - Source Breakdown

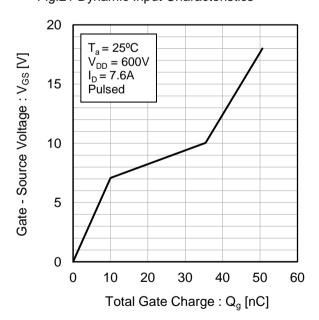
Fig.19 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Ciss Capacitance: C [pF] C_{oss} 100 C_{rss} 10 $T_a = 25^{\circ}C$ f = 1MHz $V_{GS} = 0V$ 1 1 10 100 1000 0.1 Drain - Source Voltage : V_{DS} [V]

20
T_a = 25°C

Drain - Source Voltage : V_{DS} [V]

Fig.20 C_{oss} Stored Energy

Fig.21 Dynamic Input Characteristics



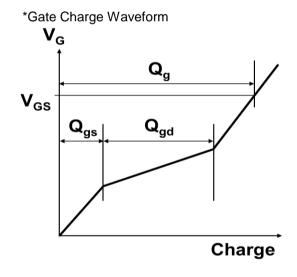


Fig.22 Typical Switching Time vs. External Gate Resistance

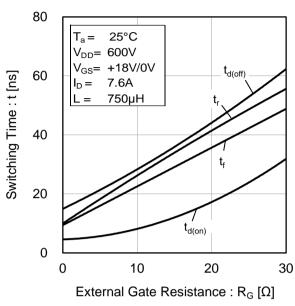


Fig.23 Typical Switching Loss vs. Drain - Source Voltage

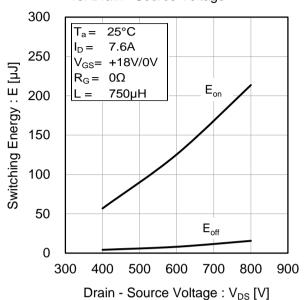


Fig.24 Typical Switching Loss vs. Drain Current

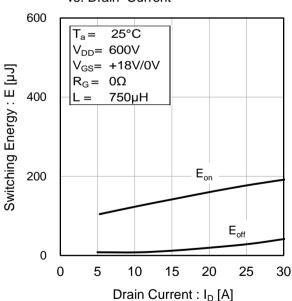
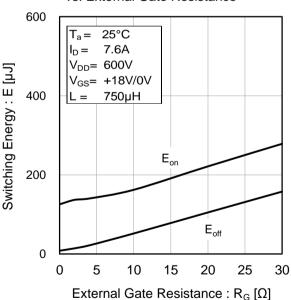


Fig.25 Typical Switching Loss vs. External Gate Resistance



Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

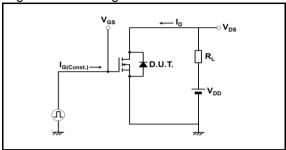


Fig.2-1 Switching Characteristics Measurement Circuit

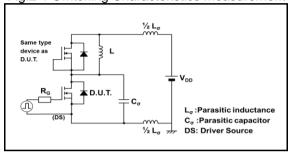


Fig.2-2 Waveforms for Switching Time

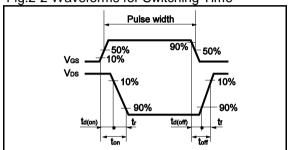


Fig.2-3 Waveforms for Switching Energy Loss

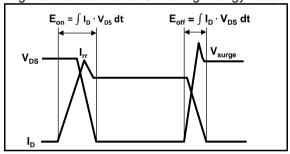


Fig.3-1 Reverse Recovery Time Measurement Circuit

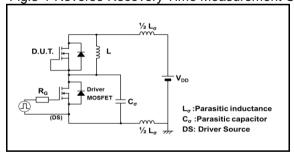
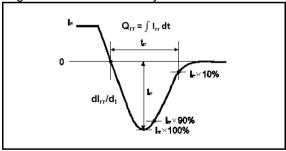


Fig.3-2 Reverse Recovery Waveform



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